

Silicon PNP Power Transistors

2SA653

DESCRIPTION

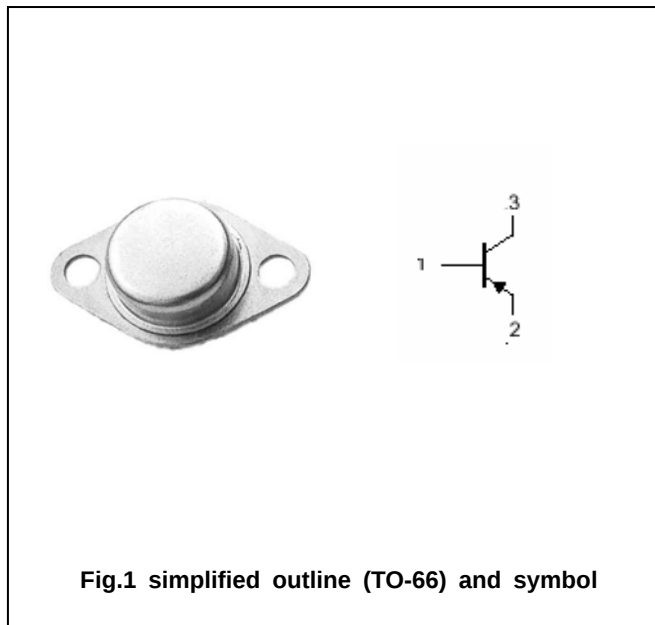
- With TO-66 package
- High voltage: $V_{CEO} = -120V(\min)$

APPLICATIONS

- Low frequency power amplifier color TV vertical deflection output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = ^\circ C$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-120	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-1.0	A
P_C	Collector power dissipation	$T_C = 25^\circ C$	15	W
T_j	Junction temperature		150	$^\circ C$
T_{stg}	Storage temperature		-55~150	$^\circ C$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA ; I _B =0	-120			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1mA ; I _E =0	-150			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-0.5A; I _B =-50mA			-1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-0.5A; I _B =-50mA			-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-150V; I _E =0			-10	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-10	μ A
h _{FE}	DC current gain	I _C =-0.2A ; V _{CE} =-5V	40			
f _T	Transition frequency	I _C =-0.1A ; V _{CE} =-10V		15		MHz

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PACKAGE OUTLINE

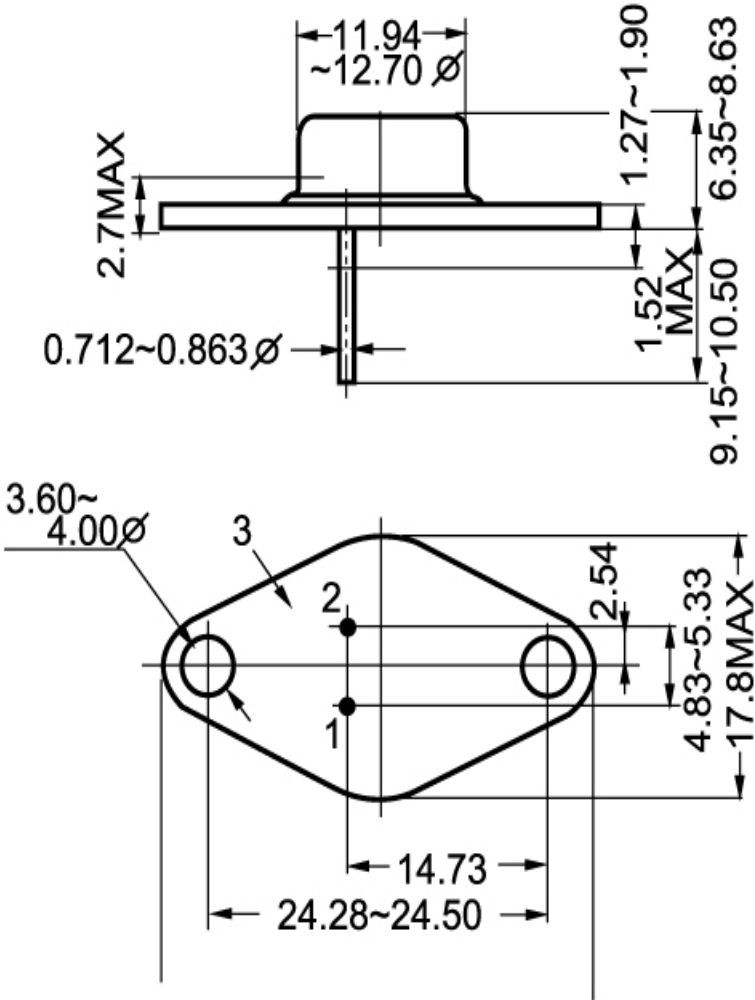


Fig.2 outline dimensions